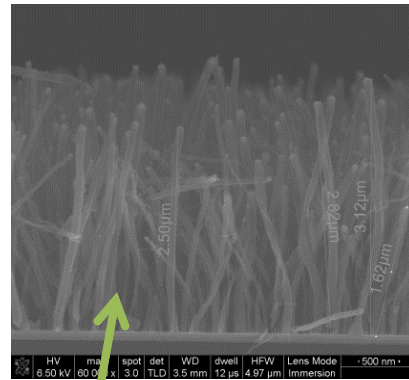
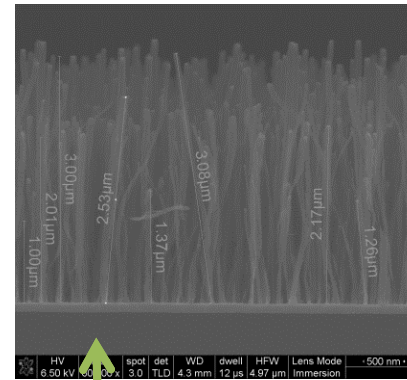


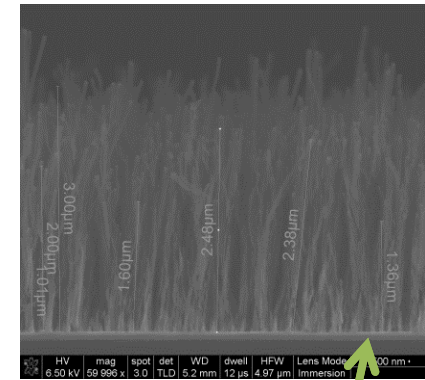
Length of CNTs on one wafer:
measured in 6 points, from the center to the edge of the wafer



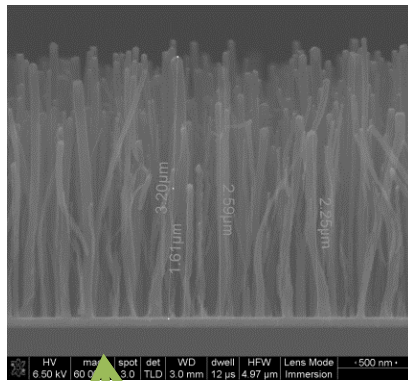
10 mm from center



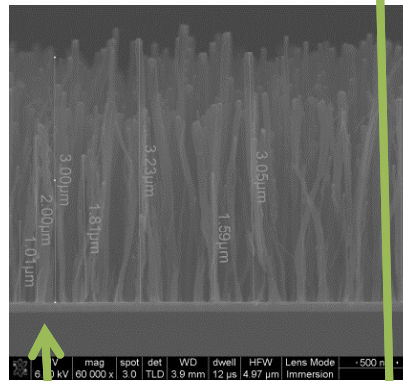
30 mm from center



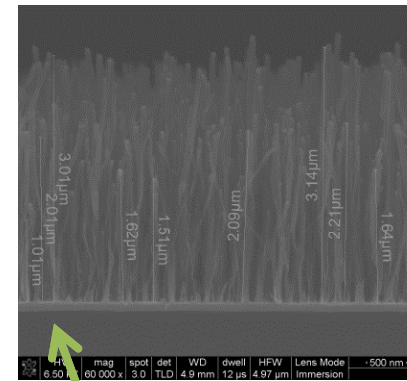
45 mm from center



Center of wafer



20 mm from center



40 mm from center

Center:
1.6-3.2
μm

+10mm
(From center):
1.6-3.1 μm

+20mm:
1.6-3.2
μm

+30mm:
1.4-3.1
μm

+40mm:
1.6-3.1
μm

+45mm:
1.3-2.5
μm

Length of the CNTs are in the ranges written above (μm)

Process parameters Recipe: PECVD NH3.txt ; **Growth time:** 10 min

Gasses growth: N2:100 sccm NH3:160 C2H2:40; **Substrate:** Si/TiW/Ni (100 nm TiW/7 nm Ni)